

Guru Ghasidas Vishwavidyalaya (A Central University Established by the Central Universities Act 2009 No. 25 of 2009) Koni, Bilaspur – 495009 (C.G.)

1.1.3

List of Employability/ Entrepreneurship/ Skill Development Courses with Course Contents

Colour Codes							
Employability Contents	Green						
Entrepreneurship Contents	Light Blue						
Skill Development Contents	Pink						
NameoftheSubjects/Related to allthreeComponents(Employability/Entrepreneurship/ SkillDevelopment)	Yellow						

गुरू घासीदास विश्वविद्यालय (हेदेव विव्वविद्यालय अधिम 2009 ह. 25 हे संगंध लागिर हेन्द्रेव विद्ववाला) कोनी, बिलासपुर - 495009 (छ.ग.)



Guru Ghasidas Vishwavidyalaya (A Central University Established by the Central Universities Ant 2009 No. 25 of 2009) Koni, Bilaspur – 495009 (C.G.)

List of Courses Focus on Employability/ Entrepreneurship/ Skill Development

Department

: Pure and applied physics

Programme Name : Batchelor of Science in Electronics

Academic Year : 2021-22

List of Courses Focus on Employability/ Entrepreneurship/Skill Development

Sr. No.	Course Code	Name of the Course
01.	PLUATT2	Basic Circuit Theory and Network Analysis
02.	PLUALT2	Basic Circuit Theory and Network Analysis Lab
03.	PLUBTT1	Semiconductor Devices
04.	PLUBLT1	Semiconductor Devices Lab
05.	PLUBTT2	Applied Physics
06.	PLUBLT2	Applied Physics Lab

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गुरू घासीदास विश्वविद्यालय (हेरीर विसरिवास अधिम 2009 व. 25 हे संतर्भ लागिर हेन्द्रीर विवरेवाल) कोनी, बिलासपुर - 495009 (छ.ग.)



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Scheme and Syllabus										
Sem	Course	Course Code	Course Name	Credits	Credits (T+L+P)	Internal Marks/	ESE Max. Marks	Total Marks		
I	Core 1	PLUATT1	Mathematical Foundation for Electronics	5	4+1+0	30	70	100		
	Core 2	PLUATT2	Basic Circuit Theory and Network Analysis	3	3+0+0	30	70	100		
		PLUALT2	Basic Circuit Theory and Network Analysis Lab	2	0+0+2	30	70	100		
	GE-1		Opted from the pool course and offered by sister Departments	5		30	70	100		
	AEC-1		Opted from the pool course and offered by University	2		30	70	100		
	SEC-1		Opted from the pool course and offered by University	2		30	70	100		
	Total		19				600			
II	Core 3	PLUBTT1	Semiconductor Devices	3	3+0+0	30	70	100		
-		PLUBLT1	Semiconductor Devices Lab	2	0+0+2	30	70	100		
	Core 4	PLUBTT2	Applied Physics	3	3+0+0	30	70	100		
		PLUBLT2	Applied Physics Lab	2	0+0+2	30	70	100		
-	GE-2		Opted from the pool course and offered by sister Departments	5		30	70	100		
	AEC-2		Opted from the pool course and offered by University	2		30	70	100		
	SEC 2		Opted from the pool course and offered by University	2		30	70	100		
	Total			19				700		

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Semester - I

Core -2: Basic Circuit Theory and Network Analysis Course Code: PLUATT2

Credits = 3 (3+0+0)

Course Objectives:

- The objective of the course is that the student acquires the knowledge of basics of electrical network.
- To gain the knowledge and critical analysis of electrical circuit using network theorem.

Course Outcomes:

- Understand the basic concepts, basic laws and methods of analysis of DC and AC networks and reduce the complexity of network using different network theorems.
- Student will understand the resonance in series and parallel circuits and also the importance of initial conditions and their evaluation.

Unit – I: Circuit Analysis: Kirchhoff's Current Law (KCL), Kirchhoff's Voltage Law (KVL), Node Analysis, Mesh Analysis, Star-Delta Conversion.

Unit – II: DC Transient Analysis: RC Circuit- Charging and discharging with initial charge, RL Circuit with Initial Current, Time Constant, RL and RC Circuits, DC Response of Series RLC Circuits.

Unit – III: AC Circuit Analysis: Sinusoidal Voltage and Current, Definition of Instantaneous, Peak, Peak to Peak, Root Mean Square and Average Values. Power in AC Circuits &Power Factor.Sinusoidal Circuit Analysis for RL, RC and RLC Circuits.Resonance in Series and Parallel RLC Circuits, Frequency Response of Series and Parallel RLC Circuits, Quality (Q) Factor and Bandwidth. Passive Filters: Low Pass, High Pass, Band Pass and Band Stop.

Unit – IV: Network Theorems: Superposition Theorem, Thevenin's Theorem, Norton's Theorem, Reciprocity Theorem, Millman's Theorem, Maximum Power Transfer Theorem. Two Port Networks: Impedance (Z) Parameters, Admittance (Y) Parameters, Transmission (ABCD) Parameters.

Reference Books:

- 1. S. A. Nasar, Electric Circuits, Schaum's outline series, Tata McGraw Hill (2004).
- 2. Electrical Circuits, M. Nahvi and J. Edminister, Schaum's Outline Series, Tata McGraw-Hill.(2005).
- 3. Robert L. Boylestad, Essentials of Circuit Analysis, Pearson Education (2004)
- 4. W. H. Hayt, J. E. Kemmerly, S. M. Durbin, Engineering Circuit Analysis, Tata McGraw Hill(2005).
- 5. Alexander and M. Sadiku, Fundamentals of Electric Circuits , McGraw Hill (2008)
- 6. Grob's Basic Electronics, 11th ed., Mitchel E. Schultz, McGraw Hill.

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Credits = 2(0+0+2)

Core - 2: Basic Circuit Theory and Network Analysis Lab

Course Code: PLUALT2

Name of Experiments

- 1. Verification of Kirchhoff's Law.
- 2. Verification of Norton's theorem.
- 3. Verification of Thevenin's Theorem.
- 4. Verification of Superposition Theorem.
- 5. Verification of the Maximum Power Transfer Theorem.
- 6. Charging and discharging of Capacitor
- 7. Designing of a Low Pass RC Filter and study of its Frequency Response.
- 8. Designing of a High Pass RC Filter and study of its Frequency Response.
- 9. Study of the Frequency Response of a Series LCR Circuit and determination of its (a) Resonant Frequency (b) Impedance at Resonance (c) Quality Factor Q (d) Band Width.
- 10. Study of the Frequency Response of a Series LCR Circuit and determination of its (a) Resonant Frequency (b) Impedance at Resonance (c) Quality Factor Q (d) Band Width.

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गुरू घासीदास विश्वविद्यालय (हेन्द्रेर रिवरिवल अधिम 2008 ह. 25 हे लंगंग लागित हेन्द्रेर रिवरेवला) कोनी, बिलासपर - 495009 (छ.ग.)



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Semester - II

Credit: 3 (3+0+0)

Core 3: Semiconductor Devices Course Code: PLUBTT1 Course Objective:

- This module introduces to the students some of the important semiconductor devices along with the underlying semiconductor physics. The module makes the students familiar with the working principles of major semiconductor diode, bipolar transistor, field-effect transistor devices, negative-resistance and power devices and photonic devices.
- Understand the fundamental principles and applications of modern electronic and optoelectronic semiconductor device.

Course Outcomes: After completion of this course, students will be able to

• Get an understanding about the working principles and characteristics of different types of semiconductor devices — p-n junction diodes, bi-polar transistors, MOSFETs, MESFETs, tunnel diodes, photo-detectors, LEDs and solar cells

Unit – I: Semiconductor Basics: Carrier Concentration at Normal Equilibrium in Intrinsic Semiconductors, Fermi Level for Intrinsic & Extrinsic Semiconductors, Donors, Acceptors, Dependence of Fermi Level on Temperature and Doping Concentration, Carrier Transport Phenomena: Carrier Drift, Mobility, Resistivity, Hall Effect, Diffusion Process, Einstein Relation, Current Density Equation, Continuity Equation.

Unit – **II: P-N Junction Diode**: Formation of Depletion Layer, Space Charge at a Junction, Derivation of Electrostatic Potential Difference at Thermal Equilibrium, Concept of Linearly Graded and an abrupt Junction, Depletion Width and Depletion Capacitance of an Abrupt Junction. Derivation of Diode Equation and I-V characteristics, Zener and Avalanche Junction Breakdown Mechanism. Tunnel diode, varactor diode, solar cell: circuit symbol, characteristics, applications.

Unit – III: Bipolar Junction Transistors (BJT): PNP and NPN Transistors, Basic Transistor Action, Emitter Efficiency, Current Gain, Energy Band Diagram of Transisto rin Thermal Equilibrium, Quantitative Modes of operation, Input and Output Characteristics of CB, CE and CC Configurations. Metal Semiconductor Junctions:

Unit – IV: Field Effect Transistors: JFET, Construction, Idea of Channel Formation, Pinch-Off and Saturation Voltage, Current-Voltage OutputCharacteristics. MOSFET, types of MOSFETs, Circuit symbols, Working and Characteristic curves of Depletion type MOSFET (both N-channel and P-Channel) and Enhancement type MOSFET (both N channel and P channel). Power Devices: UJT, Basic construction and working, Equivalent circuit, Characteristics and relaxation oscillator-expression. SCR, Construction, Working and Characteristics, MESFET, Circuit symbols, Basic constructional features, Operation and Applications.

Reference Books:

1) S. M. Sze, Semiconductor Devices: Physics and Technology, 2nd Edition, Wiley India edition (2002).

2) Ben G Streetman and S. Banerjee, Solid State Electronic Devices, Pearson Education (2006)

3) Dennis Le Croissette, Transistors, Pearson Education (1989)

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Core 3: Semiconductor Devices Lab Course Code: PLUBLT1 List of Experiments:

Credit: 2 (0+0+2)

1. Study of the I-V Characteristics of Diode – Ordinary and Zener Diode.

2. Study of the I-V Characteristics of the CE configuration of BJT and obtain r_i, r_o, β .

- 3. Study of the I-V Characteristics of the Common Base Configuration of BJT and obtain r_i , r_o , α .
- 4. Study of the I-V CharacteristicsoftheCommonCollectorConfigurationofBJTandobtainvoltagegain,
- r_i, r_o.

5. Study of the I-V Characteristics of the UJT.

- 6. Study of the I-V Characteristics of the SCR.
- 7. Study of the I-V Characteristics of JFET.
- 8. Study of the I-V Characteristics of MOSFET.
- 9. Study of Characteristics of Solar Cell

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Core 4: Applied Physics

Course Code: PLUBTT2

Course Objectives:

Understand the fundamental principles and applications of modern physics.

This course covers certain conceptual courses of physics by virtue of which the students will be able to understand some concepts of Quantum Mechanics and solid state behavior.

It also imparts the basic principles of Quantum mechanics, Thermal Properties, Debye's Law and its applications

Learning Outcomes:

Upon successful completion of this course, students will be able to address following points: Understand and explain the differences between classical and quantum mechanics. Identify behavior of the solid Materials.

Unit – I: Quantum Physics: Inadequacies of Classical physics, Compton's effect, Photo-electric Effect, Wave-particle duality, de-Broglie waves, Basic postulates and formalism of quantum mechanics: probabilistic interpretation of waves, conditions for physical acceptability of wave functions, Schrodinger wave equation for a free particle and in a force-field (1dimension),Boundary and continuity conditions, Operators in Quantum Mechanics, Conservation of probability, Time-dependent form, Linearity and superposition, Operators, Time- independent one dimensional Schrodinger wave equation, Eigen-values and Eigen functions.

Unit – **II:** Mechanical Properties of Materials: Elastic and Plastic Deformations, Hooke's Law, Elastic Moduli, Brittle and Ductile Materials, Tensile Strength, Theoretical and Critical Shear Stress of Crystals. Strengthening Mechanisms, Hardness, Creep, Fatigue, Fracture.

Unit – III: Thermal Properties, Brief Introduction to Laws of Thermodynamics, Concept of Entropy, Concept of Phonons, Heat Capacity, Debye's Law, Lattice Specific Heat, Electronic Specific Heat, Specific Heat Capacity for Si and GaAs, Thermal Conductivity, Thermoelectricity, Seebeck Effect, Thomson Effect, Peltier Effect.

Unit – **IV:** Electric and Magnetic Properties: Conductivity of metals, Ohm's Law, relaxation time, collision time and mean free path, electron scattering and resistivity of metals, heat developed in current carrying conductor, Superconductivity, Concepts of Giant Magnetic Resistance (GMR), Magnetic recording.

Reference Books:

- 1. Concepts of Modern Physics, Arthur Beiser, 2002, McGraw-Hill.
- 2. Quantum Mechanics: Theory & Applications, A. K. Ghatak & S.Lokanathan, 2004, Macmillan
- 3. Quantum Mechanics: Concepts and Applications, Wiley Publisher, Nouredine Zettili
- 4. Introduction to Solid State Physics, Charles Kittel, John Wiley & Sons, Inc
- 5. Material Science and Engineering ,5th Edition , V. Raghavan,

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Criteria – I (1.1.3)

Credit: 3 (3+0+0)



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Core 4: Applied Physics Lab Course Code: PLUBLT2 Name of the Experiments

Credit: 2 (0+0+2)

- 1. To determine the Modulus of Rigidity of a Wire by Maxwell's needle.
- 2. To determine the Young's modulus of material of cantilever.
- 3. To determine the Coefficient of Thermal Conductivity of a bad conductor by Lee and Charlton's disc method.
- 4. To study the variation of Thermo-Emf of a Thermocouple with Difference of Temperature of its Two Junctions.
- 5. Determination of Planks constant by Photo electric effect.
- 6. To determine work function of material of filament of directly heated vacuum diode.
- 7. To determine the value of e/m by (a) Magnetic focusing or (b) Bar magnet.

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